



ACE4612B

Complementary Enhancement Mode Field Effect Transistor

Description

ACE4612B uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

Features

N-channel

- $V_{DS}=30V$
- $V_{GS}=20V$
- $I_D=6A$

P-channel

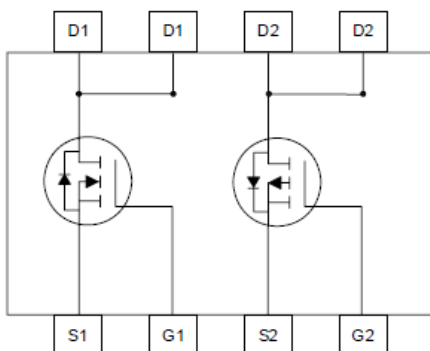
- $V_{DS}=-30V$
- $V_{GS}=20V$
- $I_D=-4A$

Absolute Maximum Ratings

Parameter	Symbol	N-channel	P-channel	Unit
Drain-Source Voltage	V_{DSS}	30	-30	V
Gate-Source Voltage	V_{GSS}	± 20	± 20	V
Continuous Drain Current (Note 1)	I_D	6	-4	A
Pulse Drain Current (Note 2)	I_{DM}	30	-30	
Total Power Dissipation (Note 1)	P_D	1	1	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^{\circ}C$

Packaging Type

SOP-8



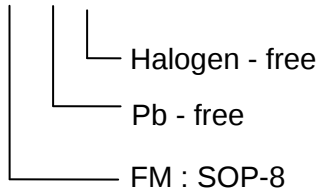


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Ordering information

ACE4612B XX + H



N-channel Electrical Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	33		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$			1	μA
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5A$		27	50	m Ω
		$V_{GS}=4.5V, I_D=5A$		39	63	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1	1.5	3	V
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$		7.3		S
Diode Forward Voltage	V_{SD}	$I_S=1A, V_{GS}=0V$		0.76		V
Turn-On Delay Time	$T_{d(on)}$	$V_{DS}=15V, V_{GS}=10V$ $R_{GEN}=3\Omega, R_L=2.3\Omega$			18	ns
Turn-Off Delay Time	$t_{d(off)}$				70	
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V$ $f=1\text{MHz}$		407		pF
Output Capacitance	C_{oss}			113		
Reverse Transfer Capacitance	C_{rss}			57		

P-channel Electrical Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	-30	-36		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	μA
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-4A$		61	65	m Ω
		$V_{GS}=-4.5V, I_D=-3A$		77	85	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	-1	-1.5	-3	V
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-4A$		12		S
Diode Forward Voltage	V_{SD}	$I_S=-1A, V_{GS}=0V$		-0.8		V
Turn-On Delay Time	$T_{d(on)}$	$V_{DS}=-15V, V_{GS}=-10V$ $R_{GEN}=3\Omega, R_L=2.5\Omega$			18	ns
Turn-Off Delay Time	$t_{d(off)}$				70	



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Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V$ $f = 1MHz$	680	pF
Output Capacitance	C_{oss}		72	
Reverse Transfer Capacitance	C_{rss}		58	

Note:

1. DUT is mounted on a 1in² FR-4 board with 2oz. Copper in a still air environment at 25°C, the current rating is based on the DC (<10s) test conditions
2. Repetitive rating, pulse width limited by junction temperature.

Typical Performance Characteristics

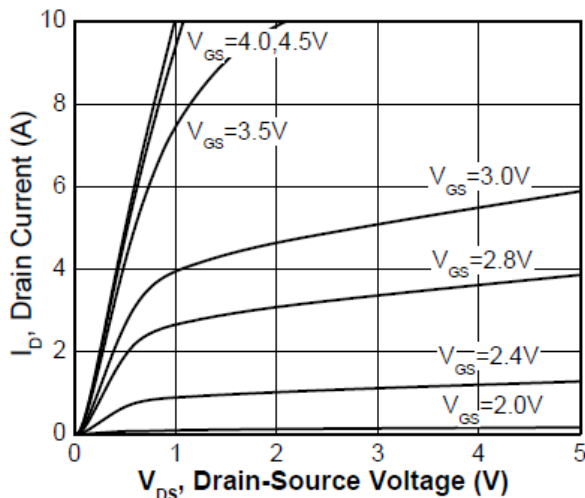


Figure 1. Output Characteristics

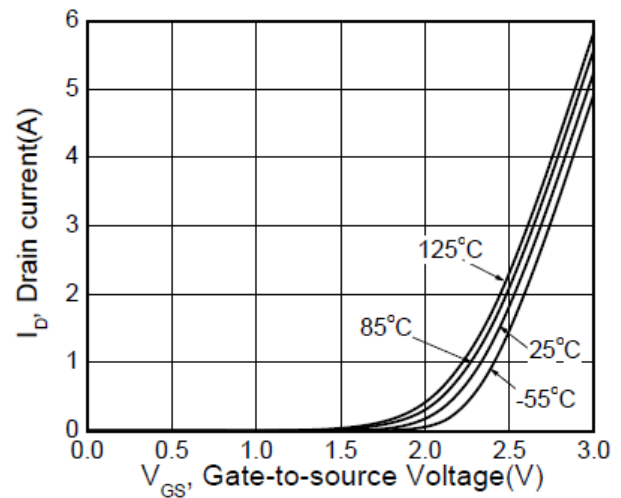


Figure 2. Transfer Characteristics

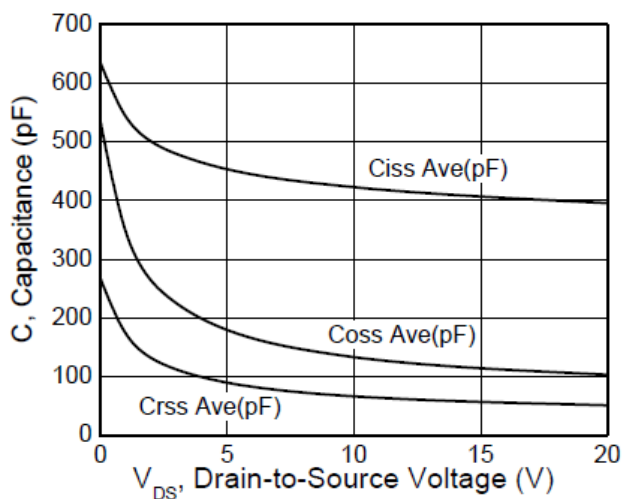


Figure 3. Capacitance

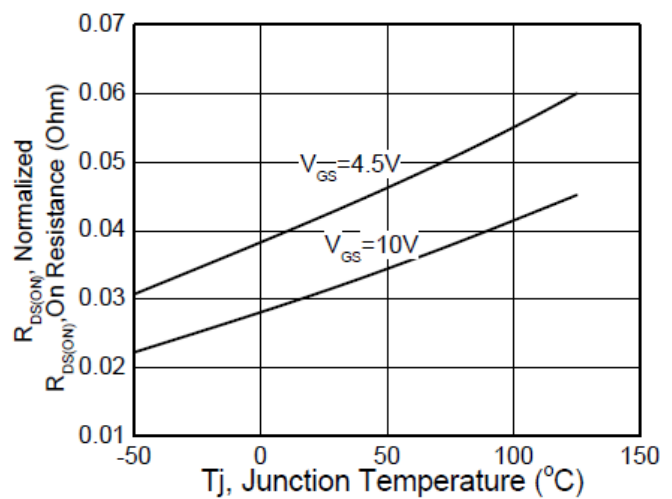


Figure 4. On Resistance Vs. Temperature



Typical Performance Characteristics

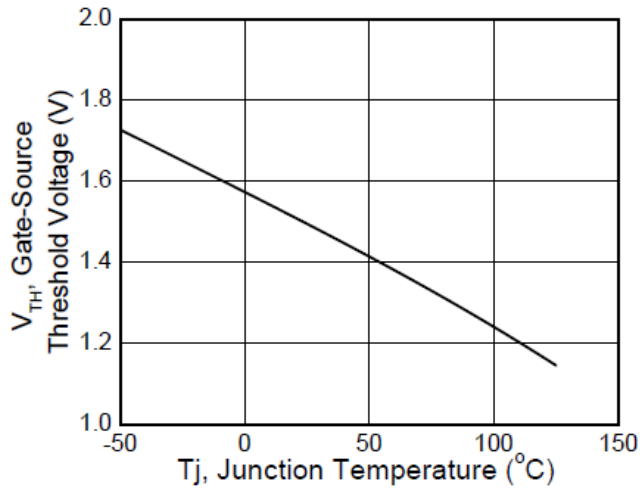


Figure 5. Gate Threshold Vs. Temperature

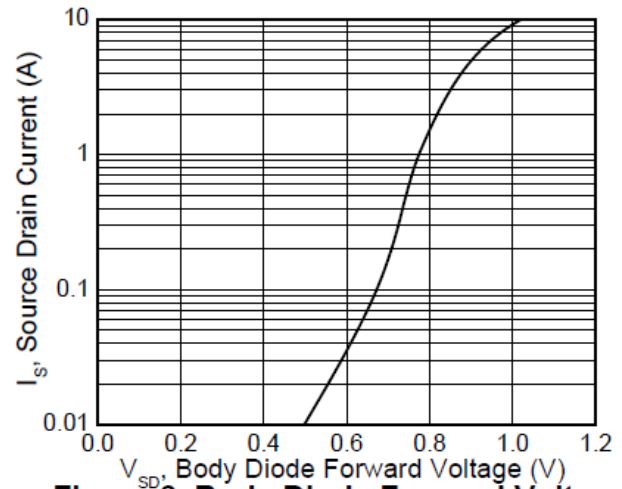


Figure 6. Body Diode Forward Voltage Vs. Source Current

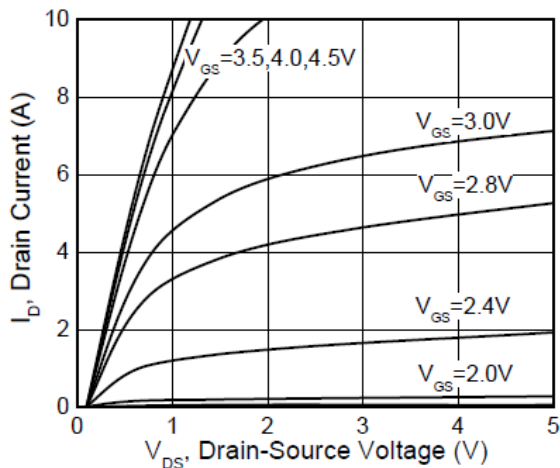


Figure 1. Output Characteristics

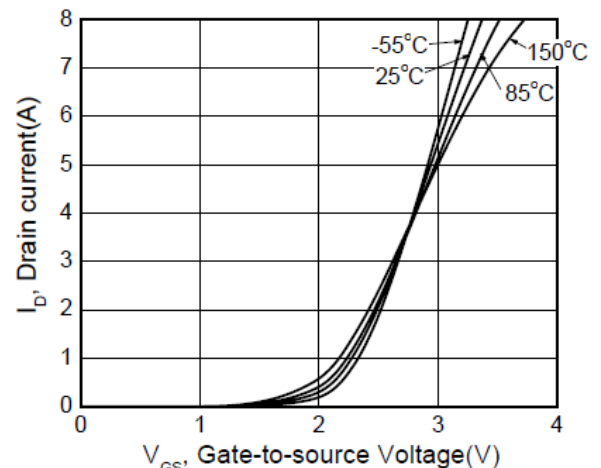


Figure 2. Transfer Characteristics

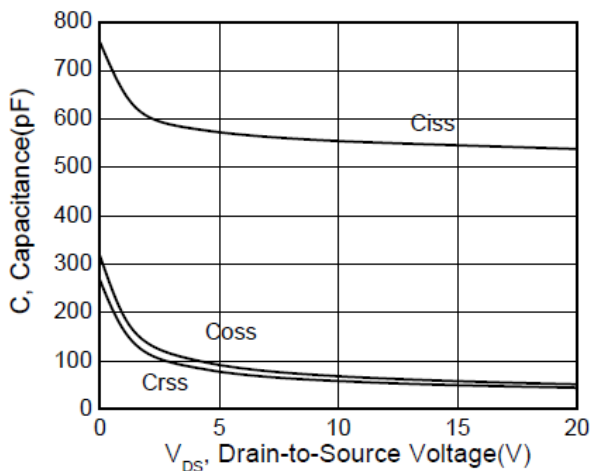


Figure 3. Capacitance

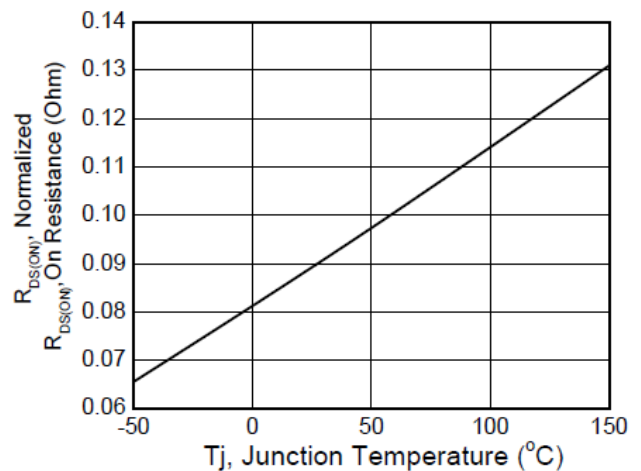


Figure 4. On Resistance Vs. Temperature



Typical Performance Characteristics

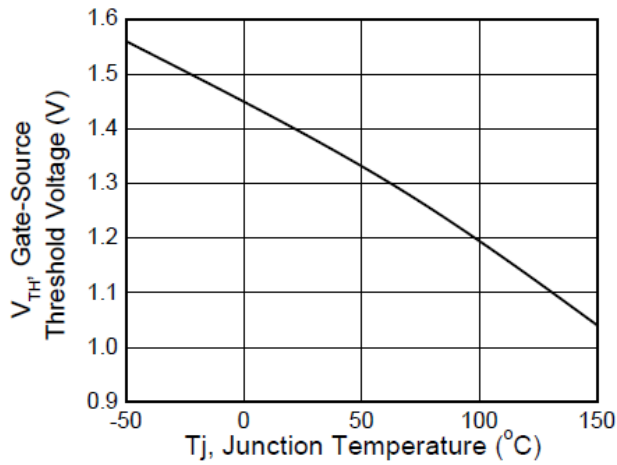


Figure 5. Gate Threshold Vs. Temperature

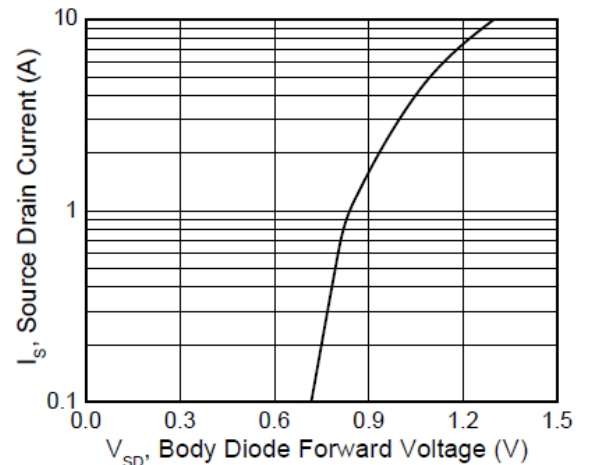
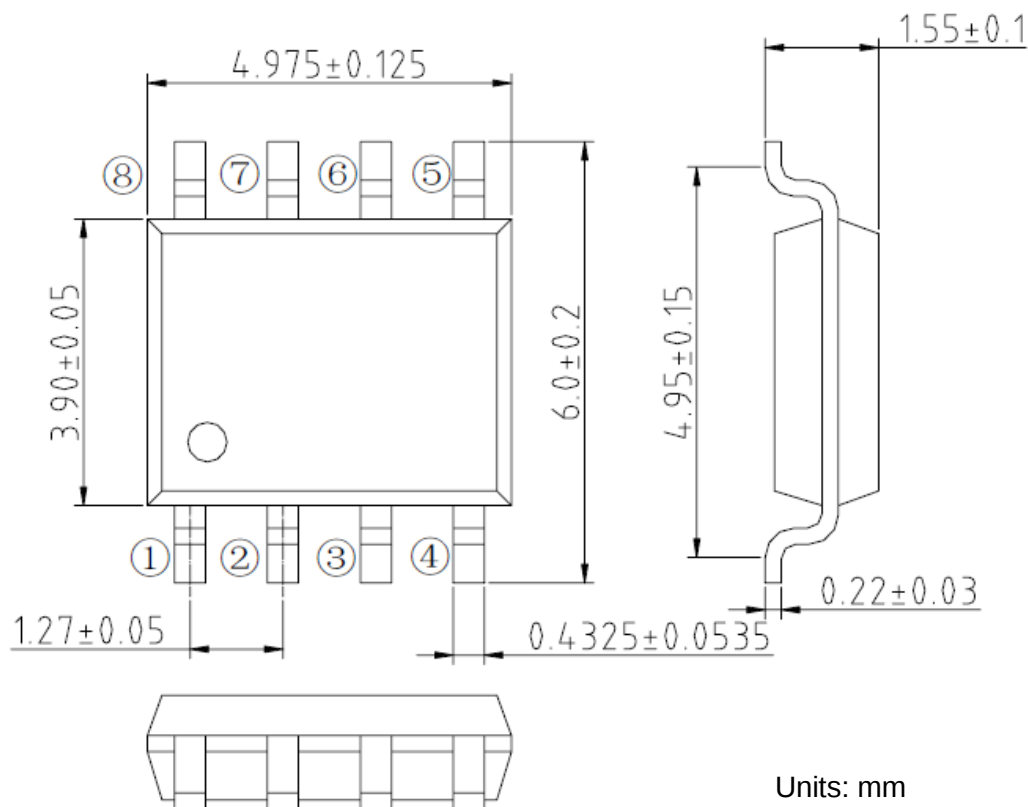


Figure 6. Body Diode Forward Voltage Vs. Source Current

Packing Information

SOP-8





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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As sued herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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